

# isc P-Channel MOSFET Transistor

## MDD3754RH

#### **FEATURES**

- Drain Current : I<sub>D</sub>= -24.4A@ T<sub>C</sub>=25 °C
- Drain Source Voltage
  - : V<sub>DSS</sub>= -40V(Min)
- Static Drain-Source On-Resistance
  - :  $R_{DS(on)} = 43m \Omega (Max) @V_{GS} = -10V$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **DESCRIPTION**

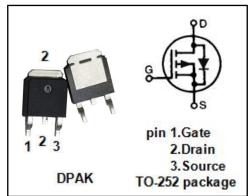
 motor drive, DC-DC converter, power switch and solenoid drive.

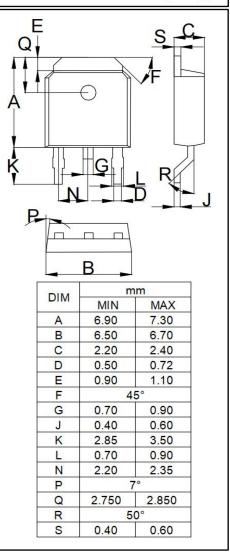
### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

ADSSESTE INACTION (Ta 25 C)							
SYMBOL	PARAMETER	VALUE	UNIT				
$V_{ extsf{DSS}}$	Drain-Source Voltage -40		V				
V <sub>GS</sub>	Gate-Source Voltage-Continuous ±20		V				
I <sub>D</sub>	Drain Current-Continuous -24.4		А				
І <sub>ОМ</sub>	Drain Current-Single Pluse	-50	А				
P <sub>D</sub>	Total Dissipation @T <sub>C</sub> =25℃	41.7	W				
TJ	Max. Operating Junction Temperature -55~150		$^{\circ}$				
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$				

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	3.0	°C/W





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#### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = -0.25mA	-40	-	V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = -0.25mA	-1.0	-3.0	V
R <sub>DS(on)1</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = -10V; I <sub>D</sub> = -6A	-	43	m Ω
R <sub>DS(on)2</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = -4.5V; I <sub>D</sub> = -4A	-	58	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0	-	±0.1	uA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -32V; V <sub>GS</sub> = 0	- -	-1.0	uA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> = -6A; V <sub>GS</sub> = 0	1	-1.2	V

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